

SANYO

No.2263A

2SB1267/2SD1903

PNP/NPN Epitaxial Planar Silicon Transistors
30V/8A High-Current Switching Applications

Applications

- Suitable for relay drivers, high-speed inverters, converters and other general high-current switching

Features

- Suitable for sets whose height is restricted
- Low collector to emitter saturation voltage:
 $V_{CE(sat)} = -0.5V(\text{PNP}), 0.4V(\text{NPN}) \text{ max}$
- Large current capacity

(): 2SB1267

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector-to-Base Voltage	V_{CB0}	(-)60	V
Collector-to-Emitter Voltage	V_{CEO}	(-)30	V
Emitter-to-Base Voltage	V_{EBO}	(-)6	V
Collector Current	I_C	(-)8	A
Peak Collector Current	i_{cp}	(-)15	A
Collector Dissipation	P_C	1.65	W
	$T_c = 25^\circ\text{C}$	30	W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

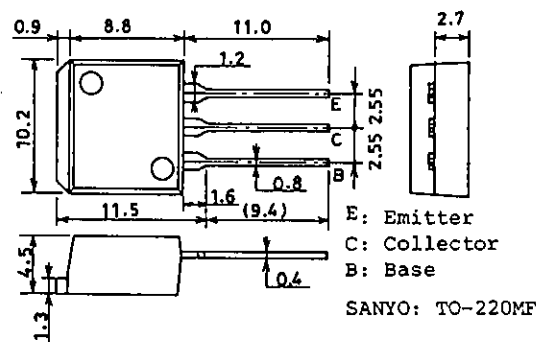
Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CB0}	$V_{CB} = (-)40V, I_E = 0$			(-)0.1	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = (-)4V, I_C = 0$			(-)0.1	mA
DC Current Gain	$h_{FE(1)}$	$V_{CE} = (-)2V, I_C = (-)1A$	70*		280*	
	$h_{FE(2)}$	$V_{CE} = (-)2V, I_C = (-)4A$	30			
Gain-Bandwidth Product	f_T	$V_{CE} = (-)5V, I_C = (-)1A$		120		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C = (-)3A, I_E = (-)0.15A$			0.4 (-0.5)	V
C-B Breakdown Voltage	$V_{(BR)CB0}$	$I_C = (-)1mA, I_E = 0$	(-)60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)30			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)1mA, I_C = 0$	(-)6			V

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Package Dimensions 2049B

(unit: mm)



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D251MH/5137TA,TS No.2263-1/4

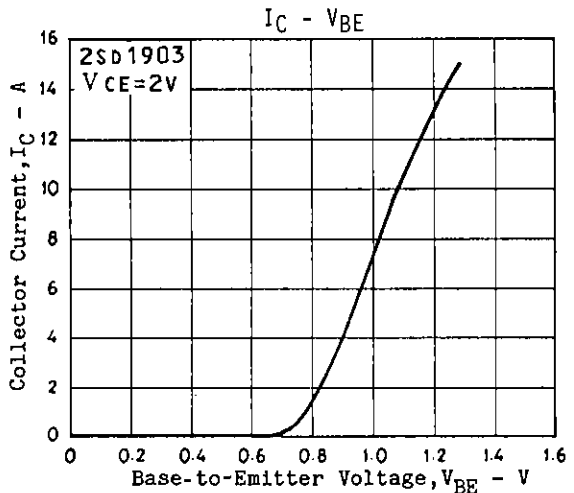
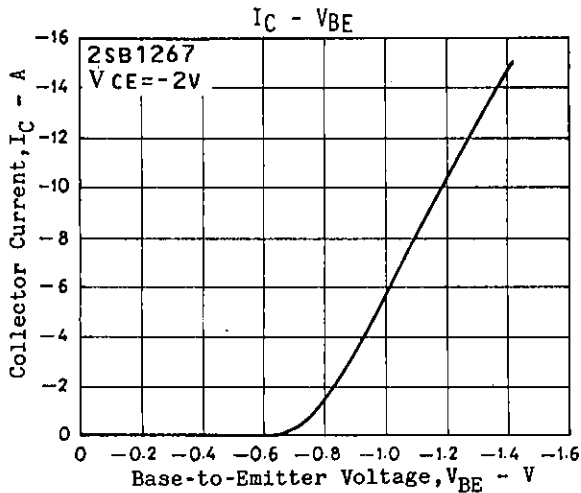
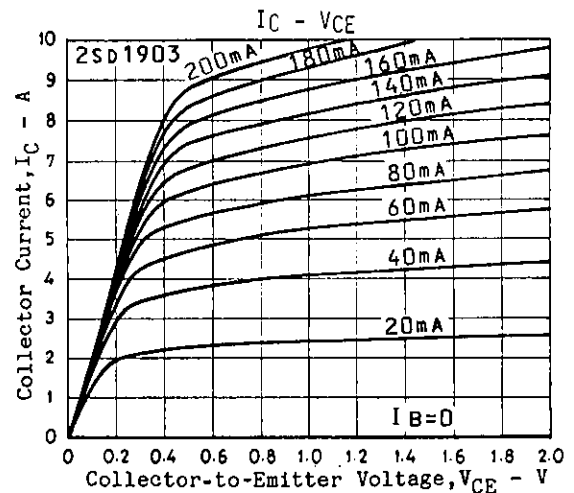
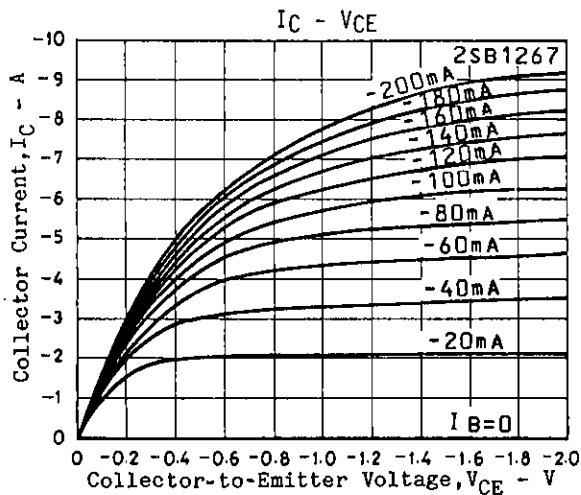
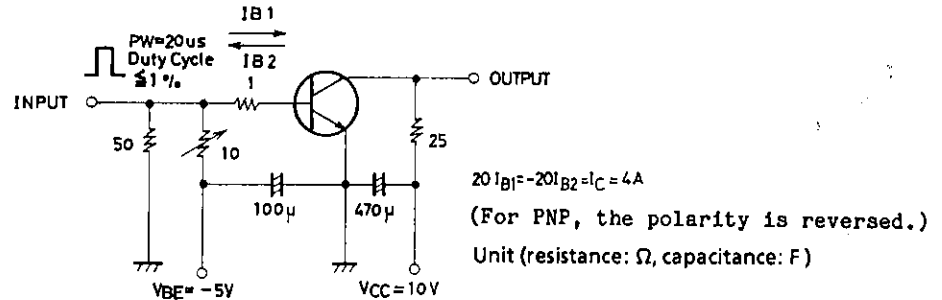
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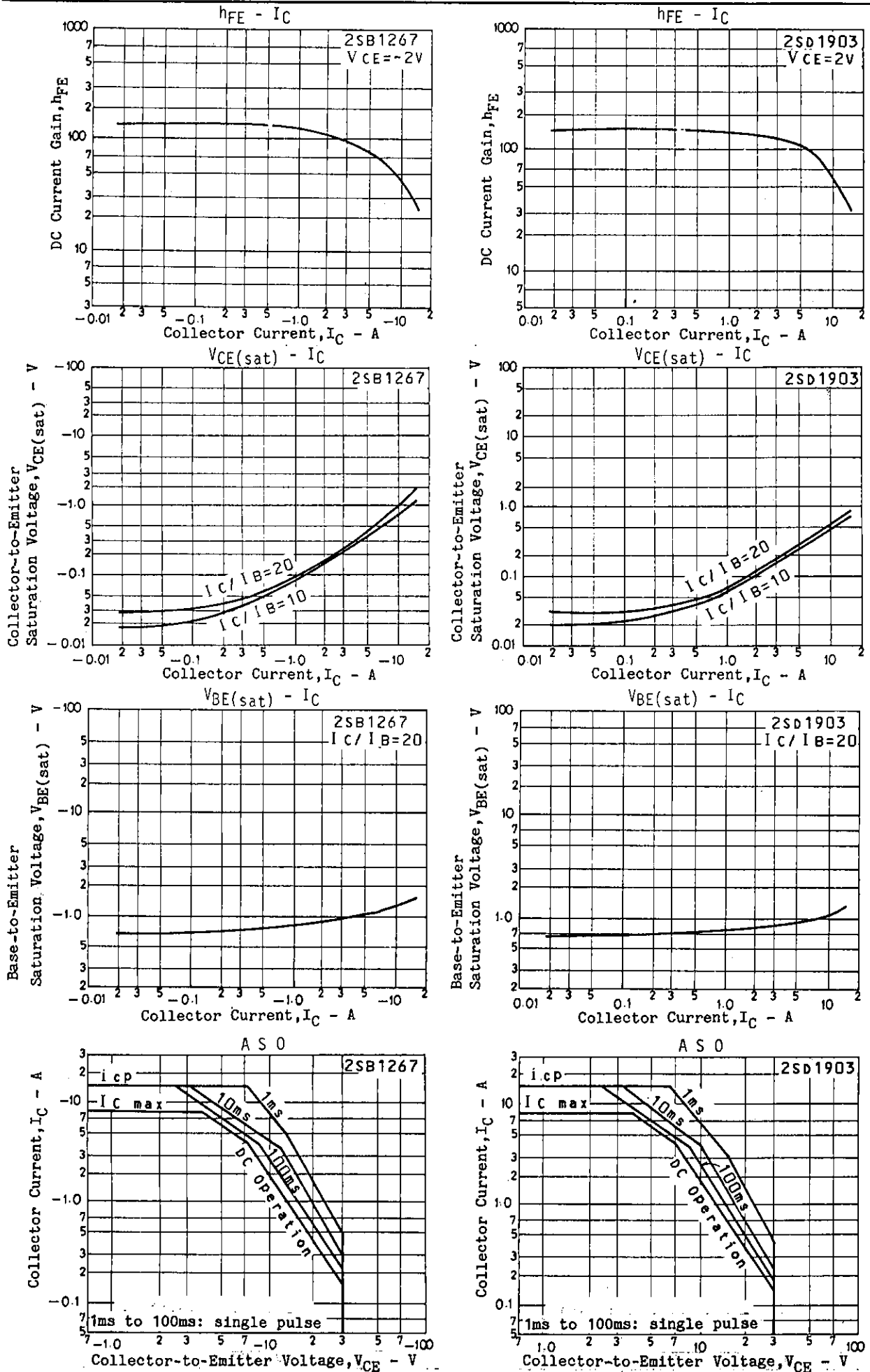
			min	typ	max	unit
Turn-on Time	t_{on}	See specified Test Circuit.		0.1		μs
Storage Time	t_{stg}	"	(0.2)	0.5		μs
Fall Time	t_f	"		0.03		μs

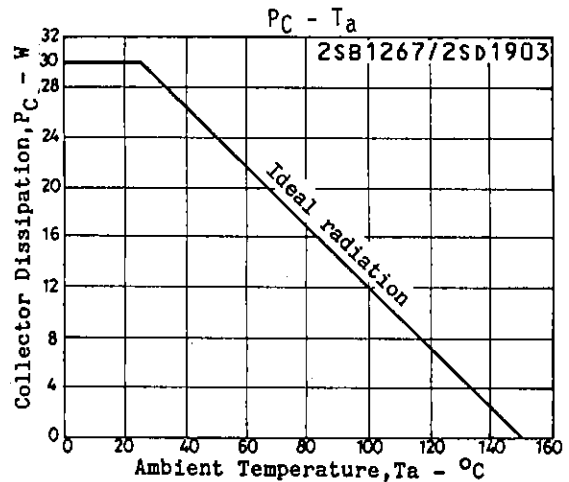
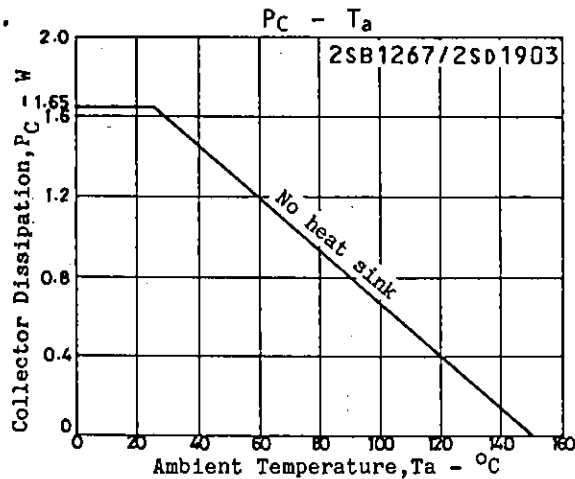
*: The 2SB1267/2SD1903 are classified by $1A h_{FE}$ as follows:

70	Q	140	100	R	200	140	S	280
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Switching Time Test Circuit







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